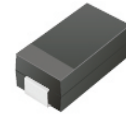




**MURA105 thru
 MURA160**

**1.0A Surface Mount Efficient Fast
 Rectifiers - 50V-600V**



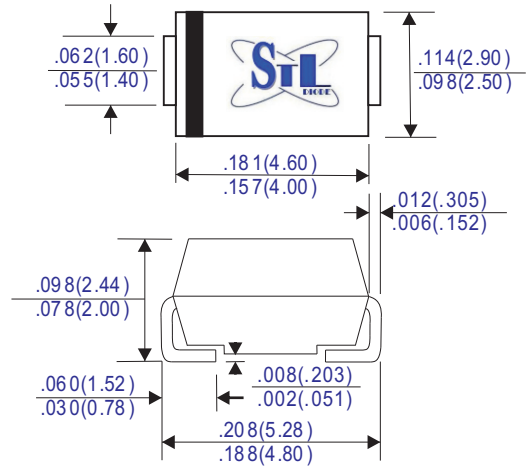
FEATURES

- Super low drop down voltage
- Ultrafast recovery time for high efficiency
- Low reverse leakage
- High surge current capability
- Glass passivated chip junction
- Low profile package for surface mounted applications
- Lead-free parts for green partner, meet RoHS requirements

MECHANICAL DATA

- Case: Molded plastic SMA/DO-214AC
- Epoxy: UL94-V0 rated flame retardant
- Terminals: Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.002 ounces, 0.064 grams

SMA (DO-214AC)



Unit :inch(mm)

MAXIMUM RATING AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	Symbols	MURA 105	MURA 110	MURA 120	MURA 140	MURA 160	Units
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	Volts
Maximum RMS Voltage	VRMS	35	70	140	280	420	Volts
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	Volts
Maximum Average Forward Rectified Current See Figure 1	I(AV)	1.0					Amps
Peak Forward Surge Current 8.3mS single half sine-wave superimposed on rated load (JEDEC Method) TL=120°C	IFSM	30.0					Amps
Maximum Instantaneous Forward Voltage at 1.0A	VF	0.875		1.1	1.25	Volts	
Maximum DC Reverse Current at Rated DC Blocking Voltage	IR	5.0 100.0		TA= 25°C TA=125°C			µA
Typical Reverse Recovery Time (Note 1)	Trr	25		35	50	µS	
Typical Junction Capacitance (Note 2)	CJ	15					pF
Typical Thermal Resistance (Note 3)	RθJL RθJA	25 75					°C/W
Operating Junction Temperature Range	TJ	-55 ~ +150					°C
Storage Temperature Range	TSTG	-55 ~ + 150					°C

Note 1. Reverse recovery test condition: IF=0.5A, IR=1.0A, IRR=0.25A

Note 2. Measured at 1.0MHz and applied reverse voltage of 4.0Volts

Note 3. Thermal resistance from junction to ambient and from junction to lead mounted on 0.2"x0.2" (5.0x5.0mm) copper and areas.

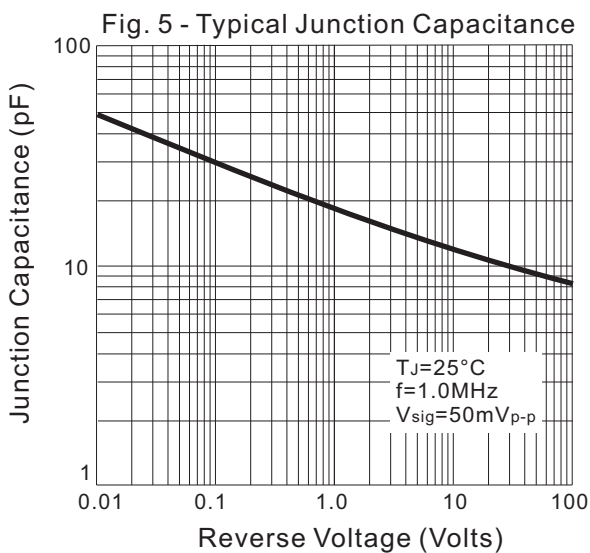
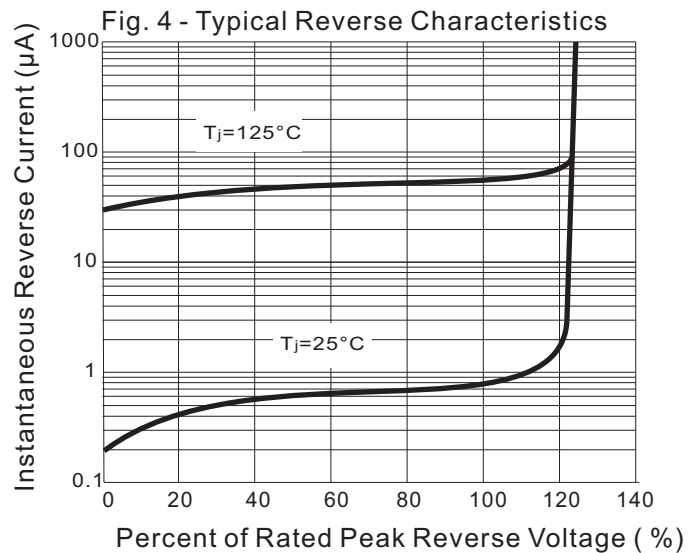
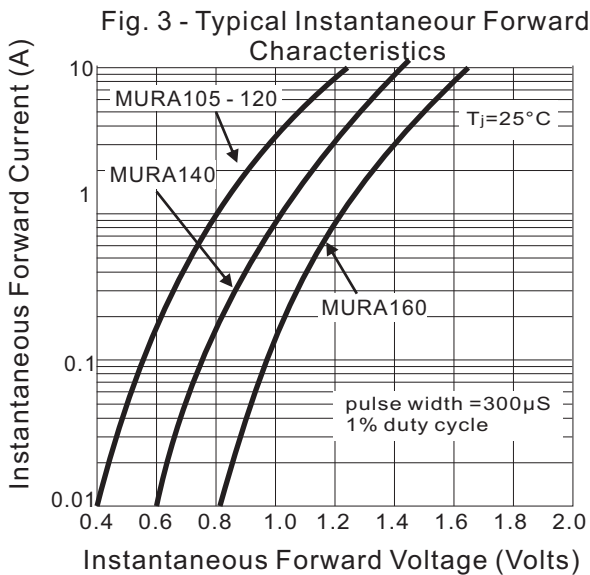
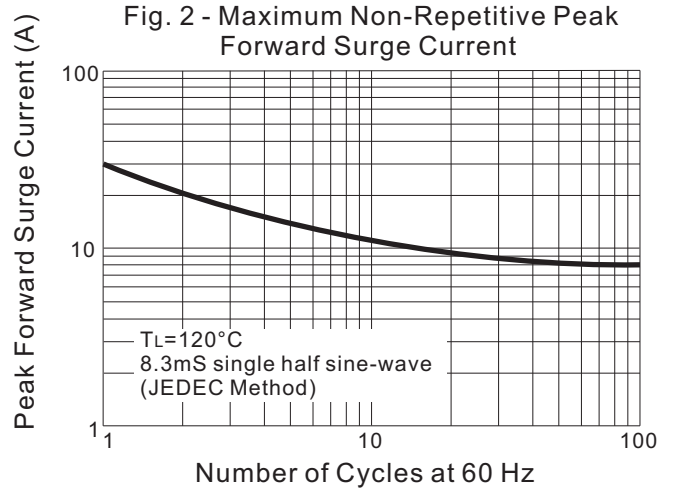
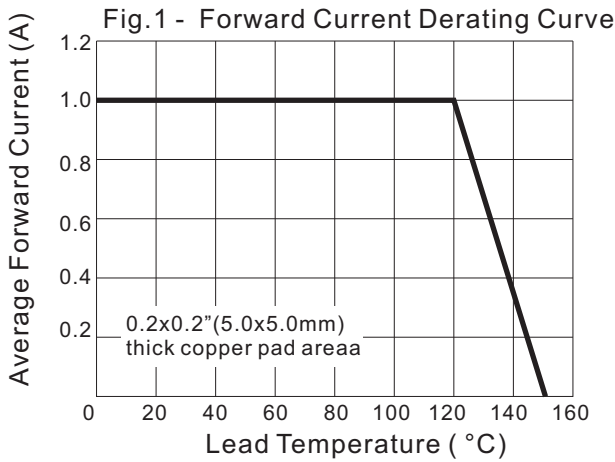
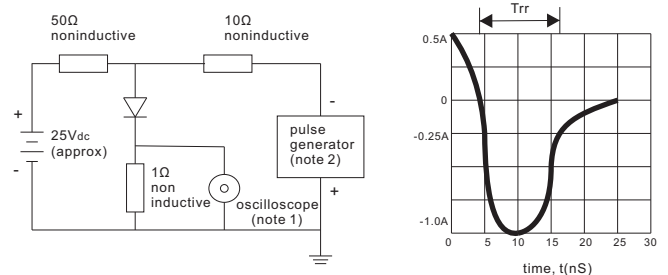


Fig. 6 - Test Circuit Diagram and Reverse Recovery Time Characteristic



Note: 1. rise time=7nS Max. input impedance=1MHz 22pF
 2. rise time=10nS Max. source impedance=80Ω